

## NCE N-Channel Enhancement Mode Power MOSFET

## **Description**

The NCE30D0808J uses advanced trench technology to provide excellent  $R_{\text{DS}(\text{ON})}$  and low gate charge. This device is suitable for use as a load switch and PWM applications.

#### **Genera Features**

•  $V_{DS} = 30V, I_D = 7.7A$ 

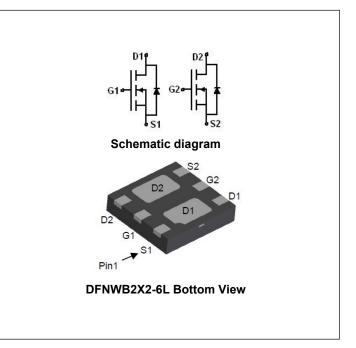
 $R_{DS(ON)}$  <26.5m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)}$  <43m $\Omega$  @  $V_{GS}$ =4.5V

- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

## **Application**

- General Purpose Interfacing Switch
- Power Management Functions



## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30D0808J	NCE30D0808J	DFNWB2X2-6L	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I <sub>D</sub>	7.7	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	31	Α
Maximum Power Dissipation	P <sub>D</sub>	2	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 150	°C

#### **Thermal Characteristic**

Thermal Resistance.Junction-to-AmbientNote 2)	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, direction to 7 this left	I VOJA	02.0	

## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	30	33	-	V



## http://www.ncepower.com

# NCE30D0808J

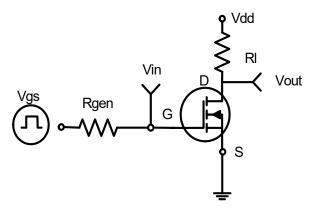
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	1	1.5	3	V
D : 0		V <sub>GS</sub> =10V, I <sub>D</sub> =7A	-	22	26.5	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	33	43	mΩ
Dynamic Characteristics (Note4)			'			
Input Capacitance	C <sub>lss</sub>	V 45VV 0V	-	558	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,	-	72.7	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	62.6	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	2.4	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =15V, $R_L$ =3 $\Omega$	-	2.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{GEN}$ =3 $\Omega$	-	9	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	2.5	-	nS
Total Gate Charge	Qg	\/ 45\/\ 5A	-	12	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =15V,I <sub>D</sub> =5A,	-	1.7	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =7.7A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	7.7	Α

## Notes:

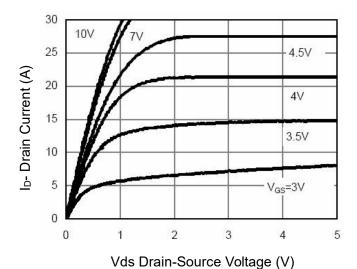
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Output Characteristics** 

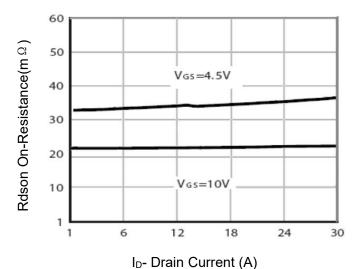


Figure 5 Drain-Source On-Resistance

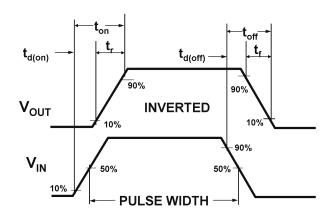
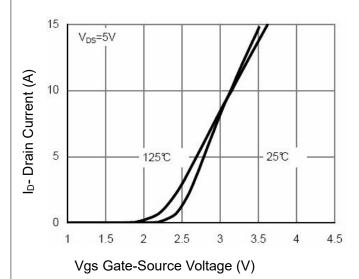


Figure 2:Switching Waveforms



**Figure 4 Transfer Characteristics** 

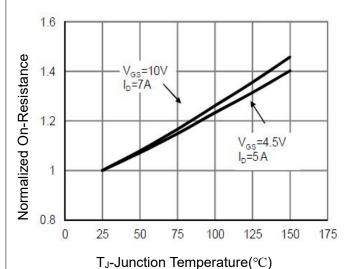
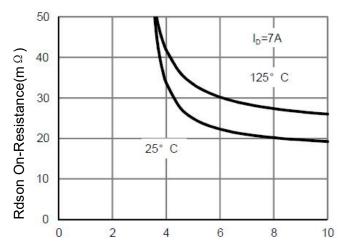


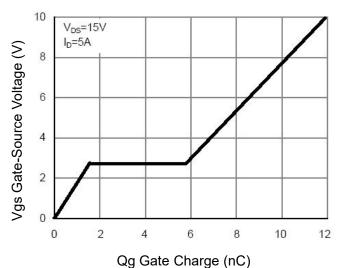
Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)

## Figure 7 Rdson vs Vgs



**Figure 9 Gate Charge** 

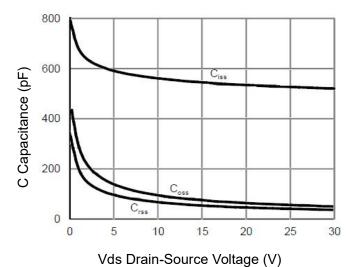
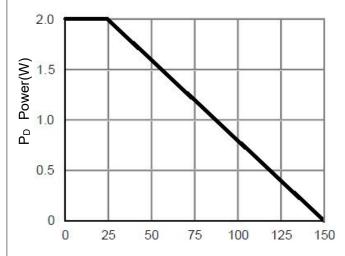


Figure 11 Capacitance vs Vds



T<sub>J</sub>-Junction Temperature(°C) **Figure 8 Power Dissipation** 

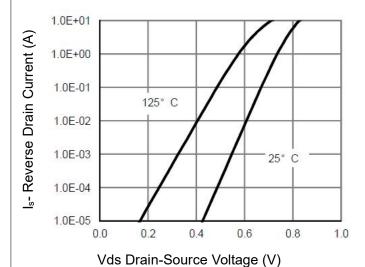
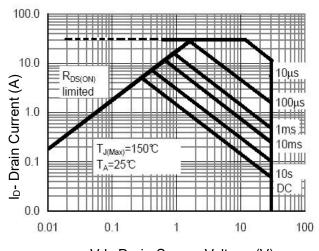
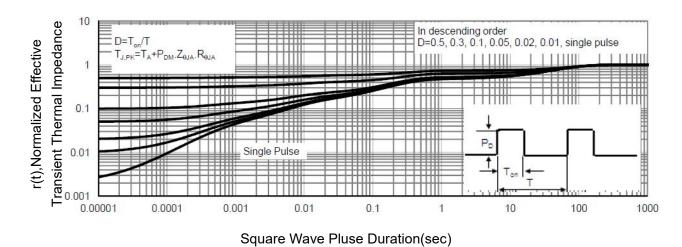


Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area

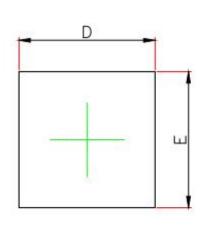


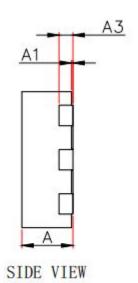


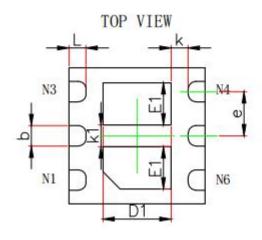
**Figure 13 Normalized Maximum Transient Thermal Impedance** 



# **DFNWB2X2-6L Package Information**







Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	MIN.	MAX.	MIN.	MAX.	
Α	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A3	0.203	REF.	0.008	REF.	
D	1.900	2.100	0.075	0.083	
E	1.900	2.100	0.075	0.083	
D1	0.900	1.100	0.035	0.043	
E1	0.520	0.720	0.020	0.028	
b	0.250	0.350	0.010	0.014	
е	0.650TYP.		0.026	STYP.	
k	0.200MIN.		0.008MIN.		
k1	0.320REF		0.013REF.		
L	0.200	0.300	0.008	0.012	

## Attention:

- Any and all NCE power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE power representative nearest you before using any NCE power products described or contained herein in such applications.
- NCE power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE power products described or contained herein.
- Specifications of any and all NCE power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE power CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE power CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. NCE power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE power product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.